

## **Description**

The IRF7201PBF uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8 (SO-8)

**General Features** 

 $V_{DS} = 30V I_{D} = 8.5A$ 

 $R_{DS(ON)}$  < 18m $\Omega$  @  $V_{GS}$ =10V



**Application** 

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

**Package Marking and Ordering Information** 

Product ID	Pack	Brand	Qty(PCS)
IRF7201PBF	SOP-8(SO-8)	HXY MOSFET	3000

# Absolute Maximum Ratings ( $T_A = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
In@T <sub>A</sub> =25°C	Continuous Drain Current <sup>1</sup>	8.5	A
In@Ta=70°C	Continuous Drain Current <sup>1</sup>	5.6	A
Ірм	Pulsed Drain Current <sup>2</sup>	35	А
EAS	Single Pulse Avalanche Energy³	20	mJ
las	Avalanche Current	20	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	1.5	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
	Thermal Resistance Junction-ambient¹(t≤10s)	85	°C/W
$R_{ hetaJA}$	Thermal Resistance Junction-ambient <sup>1</sup>	25	°C/W



# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V	
$\triangle BV_{DSS} \! / \! \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.034		V/°C	
D	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =7A	1	14	18	$$ m $\Omega$	
R <sub>DS(ON)</sub>	Static Dialii-Source Off-Nesistance	V <sub>GS</sub> =4.5V , I <sub>D</sub> =4A		20	26		
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.5	2.5	V	
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	VGS-VDS , ID -250UA	1	-3.84		mV/°C	
less	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	- uA	
Ipss		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5		
Igss	Gate-Source Leakage Current	$V_{GS}=\pm 20V$ , $V_{DS}=0V$			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =7A		6.2		S	
$R_g$	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.04	2.1	Ω	
Qg	Total Gate Charge (4.5V)			6	8.4		
$Q_{gs}$	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =7A		2.2	3.1	nC	
$Q_{gd}$	Gate-Drain Charge			2	2.8		
$T_{d(on)}$	Turn-On Delay Time			1.2	2.4		
T <sub>r</sub>	Rise Time	$V_{DD}$ =15V , $V_{GS}$ =10V , $R_{G}$ =3.3 $\Omega$		40	72.0	ns	
$T_{d(off)}$	Turn-Off Delay Time	I <sub>D</sub> =7A		18	36.0		
Tf	Fall Time			7.2	14.4		
Ciss	Input Capacitance			583	816.2		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		77	107.8	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			59	82.6		
ls	Continuous Source Current <sup>1,5</sup>	\\ -\\ -0\\   Farras Correct			7	Α	
Ism	Pulsed Source Current <sup>2,5</sup>	──V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			35	Α	
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V	
t <sub>rr</sub>	Reverse Recovery Time			7.2		nS	
Qrr	Reverse Recovery Charge	IF=7A,dI/dt=100A/µs,T <sub>J</sub> =25°C		2.9		nC	

#### Note:

<sup>1.</sup> The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

<sup>2.</sup>The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%

<sup>3.</sup> The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =20A

<sup>4.</sup>The power dissipation is limited by 150°C junction temperature

<sup>5.</sup> The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



# **Typical Characteristics**

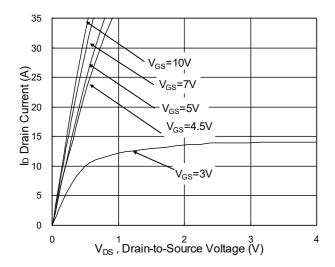


Fig.1 Typical Output Characteristics

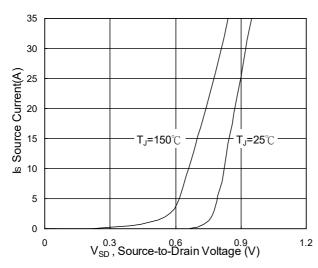


Fig.3 Forward Characteristics Of Reverse

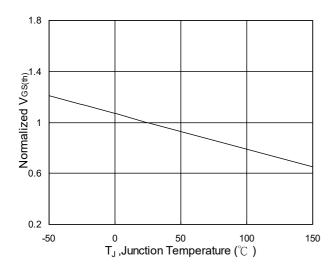


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$ 

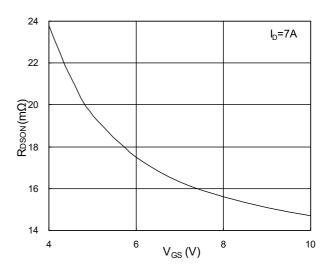


Fig.2 On-Resistance vs. Gate-Source

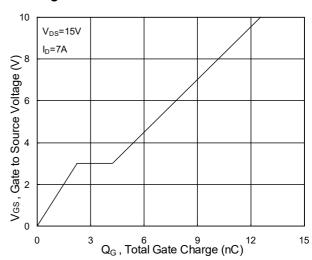


Fig.4 Gate-Charge Characteristics

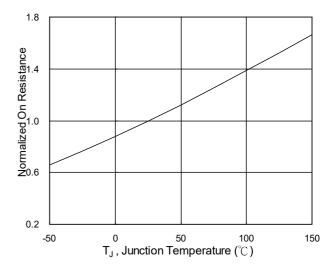
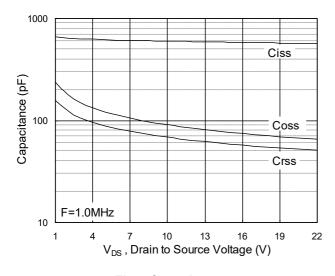


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





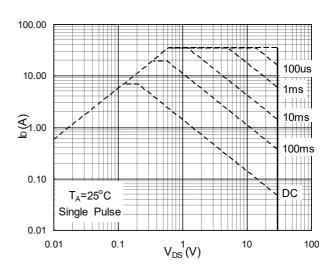


Fig.7 Capacitance

Fig.8 Safe Operating Area

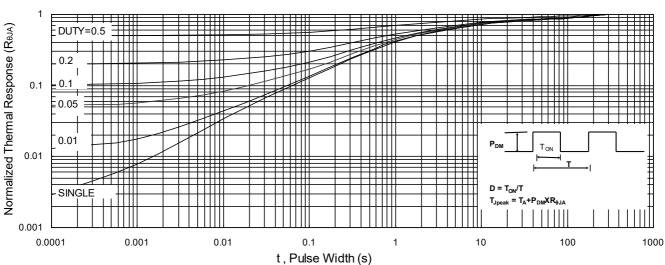


Fig.9 Normalized Maximum Transient Thermal Impedance

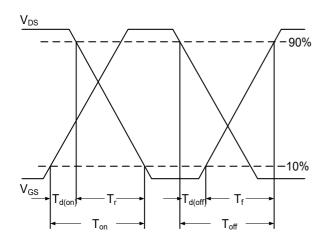


Fig.10 Switching Time Waveform

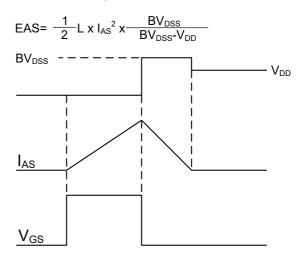
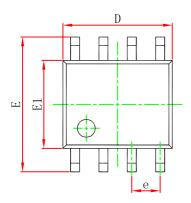
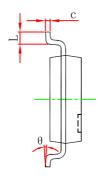


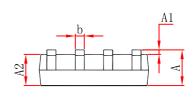
Fig.11 Unclamped Inductive Switching Waveform



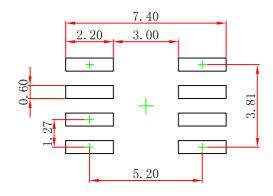
# **SOP-8(SO-8) Package Outline Dimensions**







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	1. 350	1.750	0.053	0.069	
A1	0.100	0. 250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0. 020	
c	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0. 197	
e	1. 270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



- Note:
  1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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